

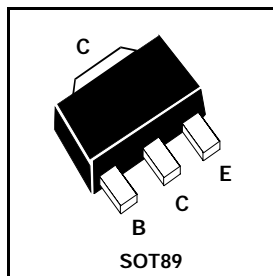
SOT89 NPN SILICON PLANAR DARLINGTON TRANSISTOR

ISSUE 4 – JANUARY 1996

BCV29

COMPLEMENTARY TYPE – BCV28

PARTMARKING DETAIL – EF



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	10	V
Peak Pulse Current	I_{CM}	800	mA
Continuous Collector Current	I_C	500	mA
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	1	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-65 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb}=25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	40			V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	30			V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	10			V	$I_E=10\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			100 10	nA μA	$V_{CB}=30\text{V}$ $V_{CB}=30\text{V}, T_{amb}=150^\circ\text{C}$
Emitter Cut-Off Current	I_{EBO}			100	nA	$V_{EB}=4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			1	V	$I_C=100\text{mA}, I_B=0.1\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1.5	V	$I_C=100\text{mA}, I_B=0.1\text{mA}^*$
Static Forward Current Transfer Ratio	h_{FE}	4000 10000 20000 4000				$I_C=100\mu\text{A}, V_{CE}=1\text{V}\dagger$ $I_C=10\text{mA}, V_{CE}=5\text{V}^*$ $I_C=100\text{mA}, V_{CE}=5\text{V}^*$ $I_C=500\text{mA}, V_{CE}=5\text{V}^*$
Transition Frequency	f_T		150		MHz	$I_C=50\text{mA}, V_{CE}=5\text{V}$ $f=20\text{MHz}$
Output Capacitance	C_{obo}		3.5		pF	$V_{CB}=10\text{V}, f=1\text{MHz}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
 For typical graphs see FMMT38A datasheet † Periodic Sample Test Only
 Spice parameter data is available upon request for this device